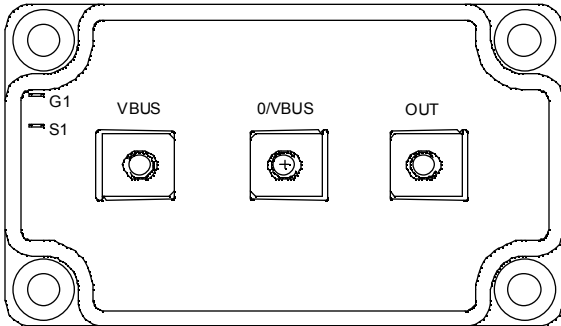
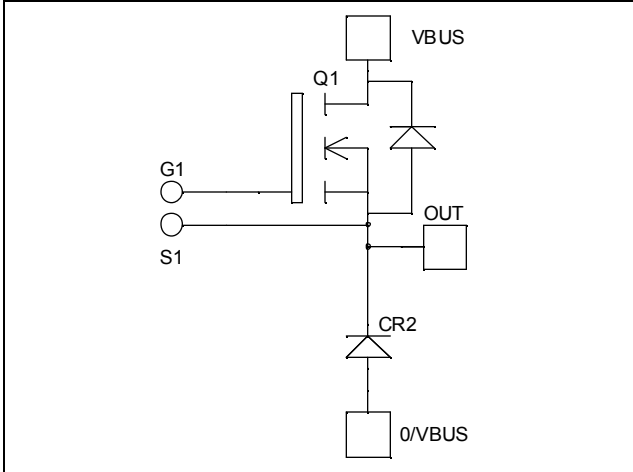


***Buck chopper  
MOSFET Power Module***

**$V_{DSS} = 1000V$   
 $R_{DSon} = 90m\Omega \text{ max @ } T_j = 25^\circ C$   
 $I_D = 78A \text{ @ } T_c = 25^\circ C$**



**Application**

- AC and DC motor control
- Switched Mode Power Supplies

**Features**

- Power MOS 7<sup>®</sup> MOSFETs
  - Low  $R_{DSon}$
  - Low input and Miller capacitance
  - Low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - M5 power connectors
- High level of integration

**Benefits**

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile

**Absolute maximum ratings**

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	1000	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	78
		$T_c = 80^\circ C$	59
$I_{DM}$	Pulsed Drain current	312	
$V_{GS}$	Gate - Source Voltage	$\pm 30$	V
$R_{DSon}$	Drain - Source ON Resistance	90	m $\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	1250
$I_{AR}$	Avalanche current (repetitive and non repetitive)	25	A
$E_{AR}$	Repetitive Avalanche Energy	50	mJ
$E_{AS}$	Single Pulse Avalanche Energy	3000	

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

## Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$BV_{DSS}$	Drain - Source Breakdown Voltage	$V_{GS} = 0V, I_D = 1mA$	1000			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 1000V$   $T_j = 25^\circ\text{C}$			1	mA
		$V_{GS} = 0V, V_{DS} = 800V$   $T_j = 125^\circ\text{C}$			3	
$R_{DS(on)}$	Drain - Source on Resistance	$V_{GS} = 10V, I_D = 39A$			90	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 10mA$	3		5	V
$I_{GSS}$	Gate - Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			$\pm 250$	nA

## Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1MHz$		20.7		nF
$C_{oss}$	Output Capacitance			3.5		
$C_{rss}$	Reverse Transfer Capacitance			0.64		
$Q_g$	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 500V$ $I_D = 78A$		744		nC
$Q_{gs}$	Gate - Source Charge			96		
$Q_{gd}$	Gate - Drain Charge			488		
$T_{d(on)}$	Turn-on Delay Time	<b>Inductive switching @ <math>125^\circ\text{C}</math></b> $V_{GS} = 15V$ $V_{Bus} = 670V$ $I_D = 78A$ $R_G = 1.2\Omega$		18		ns
$T_r$	Rise Time			12		
$T_{d(off)}$	Turn-off Delay Time			155		
$T_f$	Fall Time			40		
$E_{on}$	Turn-on Switching Energy ❶	<b>Inductive switching @ <math>25^\circ\text{C}</math></b> $V_{GS} = 15V, V_{Bus} = 670V$ $I_D = 78A, R_G = 1.2\Omega$		3.6		mJ
$E_{off}$	Turn-off Switching Energy ❷			2.5		
$E_{on}$	Turn-on Switching Energy ❶	<b>Inductive switching @ <math>125^\circ\text{C}</math></b> $V_{GS} = 15V, V_{Bus} = 670V$ $I_D = 78A, R_G = 1.2\Omega$		5.7		mJ
$E_{off}$	Turn-off Switching Energy ❷			3.1		

## Diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{F(AV)}$	Maximum Average Forward Current	50% duty cycle   $T_c = 70^\circ\text{C}$		100		A
$V_F$	Diode Forward Voltage	$I_F = 100A$		1.9	2.5	V
		$I_F = 200A$		2.2		
		$I_F = 100A$   $T_j = 125^\circ\text{C}$		1.7		
$t_{rr}$	Reverse Recovery Time	$I_F = 100A$ $V_R = 667V$ $di/dt = 200A/\mu s$   $T_j = 25^\circ\text{C}$		300		ns
		$T_j = 125^\circ\text{C}$		360		
$Q_{rr}$	Reverse Recovery Charge	$I_F = 100A$ $V_R = 667V$ $di/dt = 200A/\mu s$   $T_j = 25^\circ\text{C}$		800		nC
		$T_j = 125^\circ\text{C}$		4050		

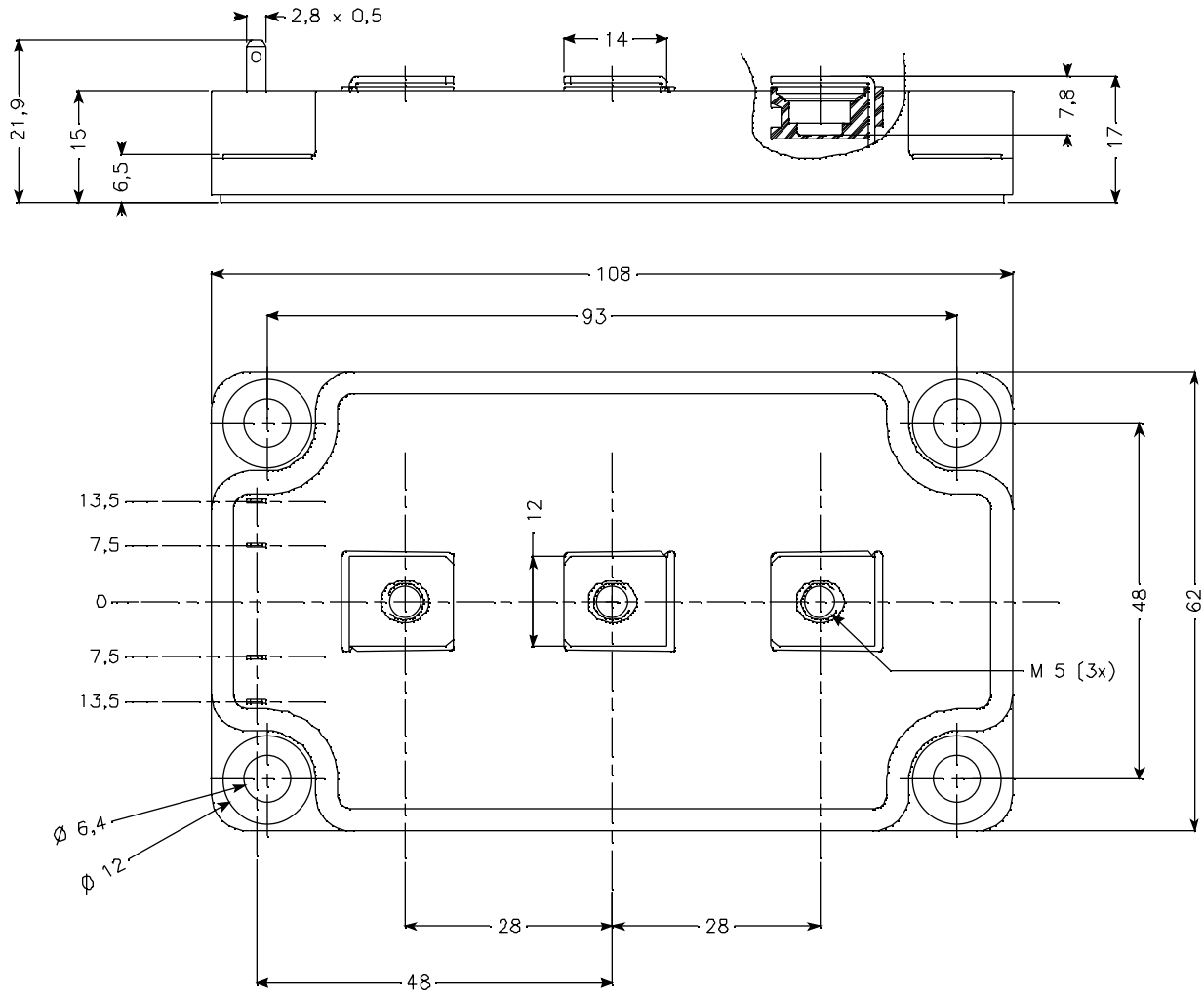
❶  $E_{on}$  includes diode reverse recovery.

❷ In accordance with JEDEC standard JESD24-1.

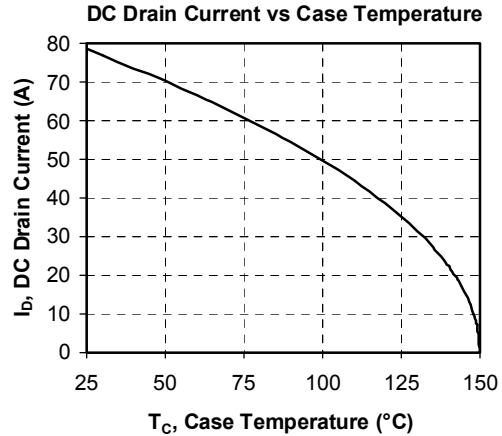
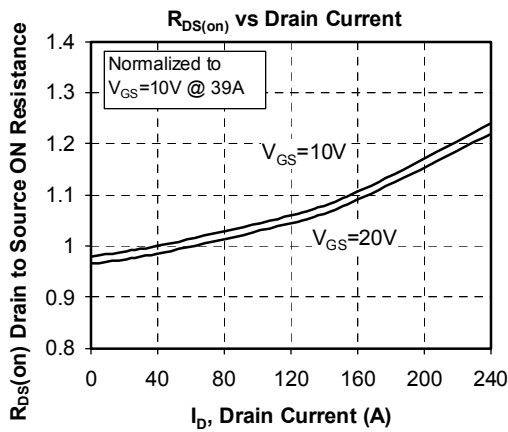
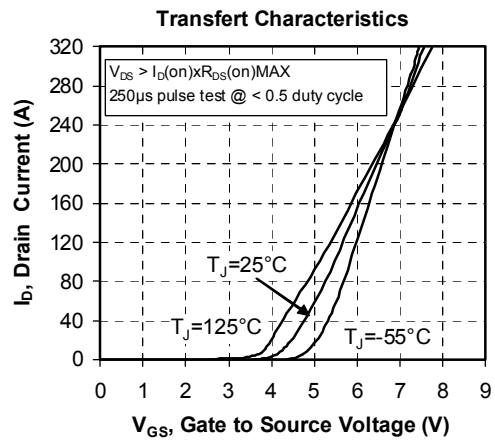
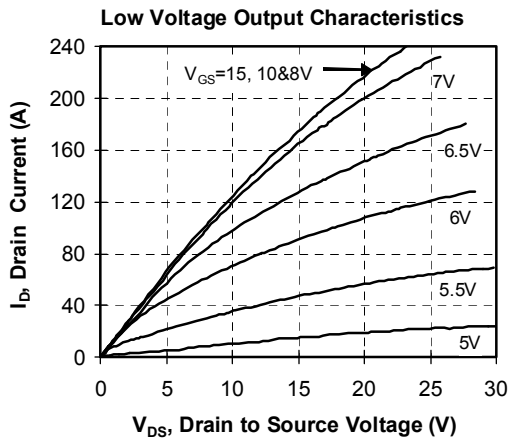
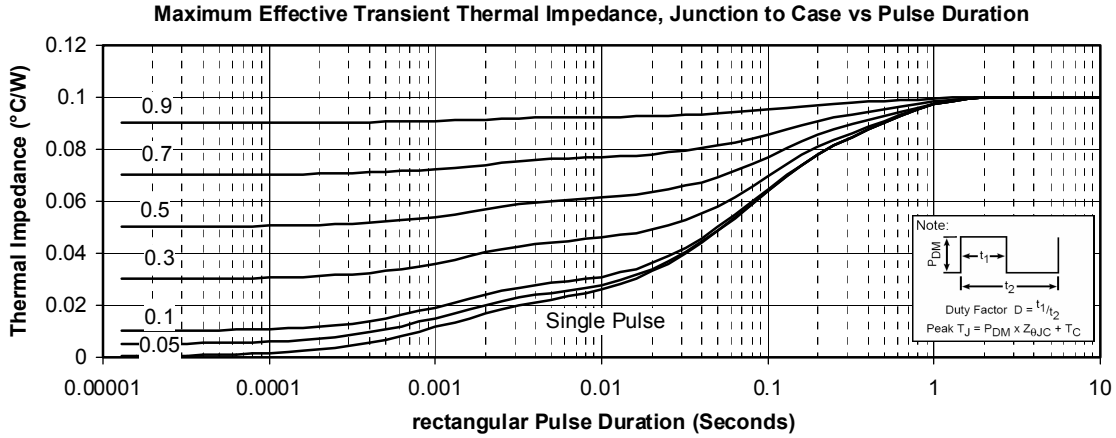
**Thermal and package characteristics**

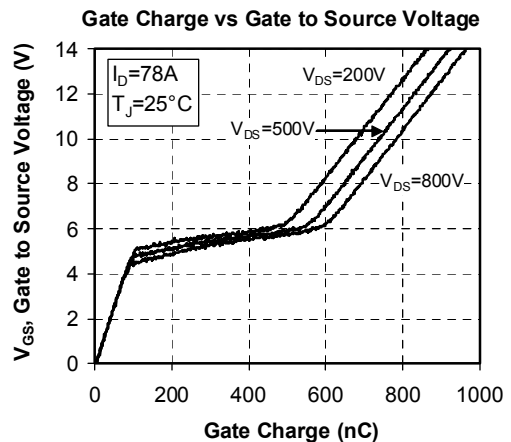
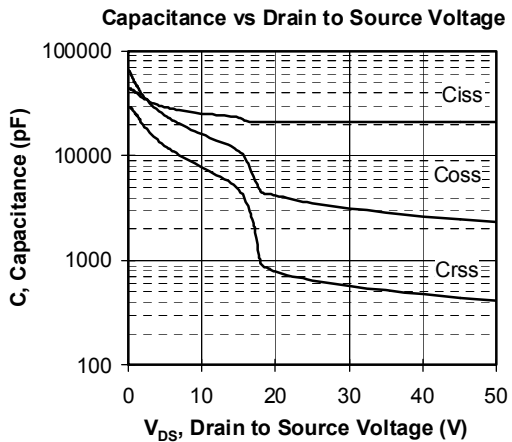
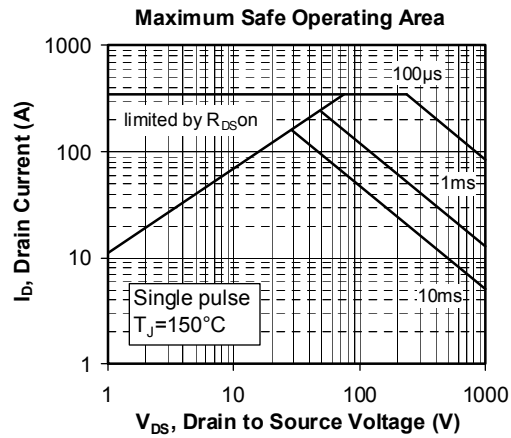
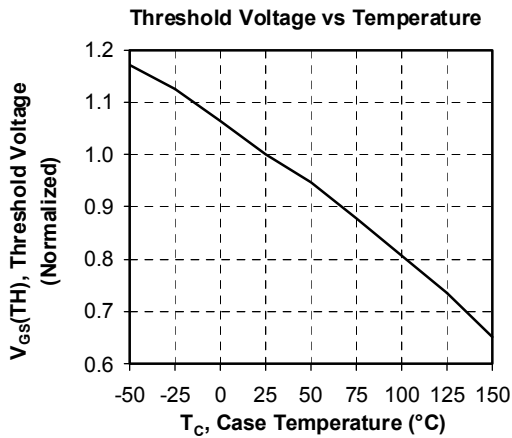
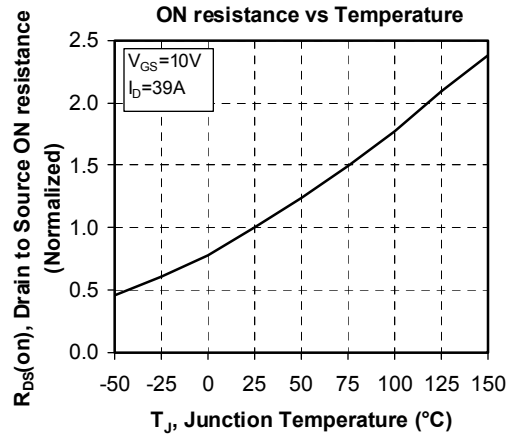
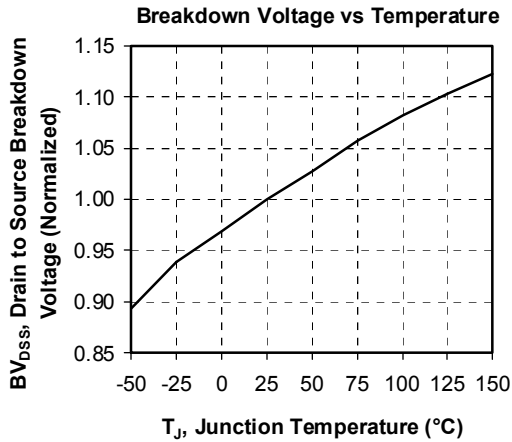
Symbol	Characteristic		Min	Typ	Max	Unit
R <sub>thJC</sub>	Junction to Case	Transistor			0.1	°C/W
		Diode			0.6	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t = 1 min, I <sub>isol</sub> < 1mA, 50/60Hz		2500			V
T <sub>J</sub>	Operating junction temperature range		-40		150	°C
T <sub>STG</sub>	Storage Temperature Range		-40		125	
T <sub>C</sub>	Operating Case Temperature		-40		100	
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package Weight				280	g

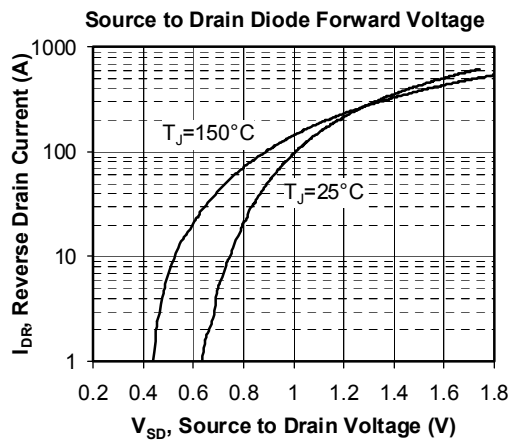
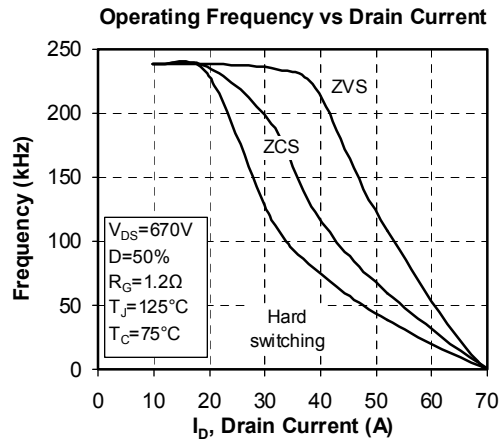
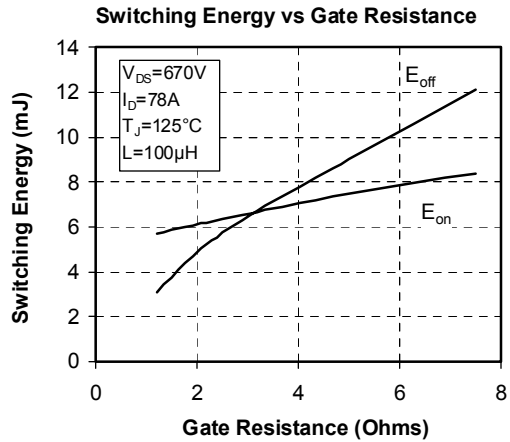
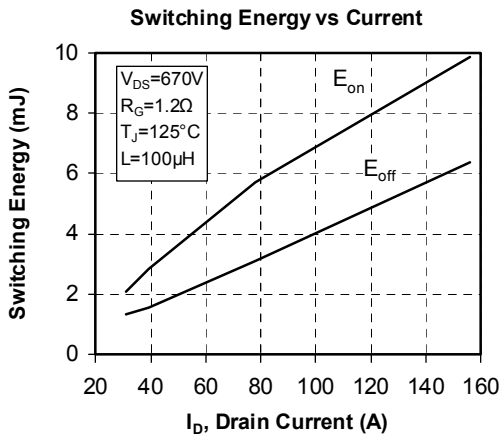
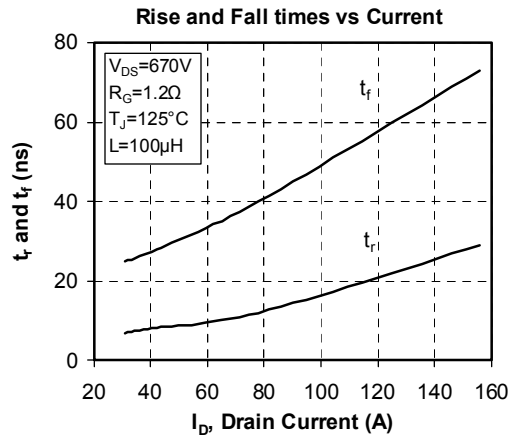
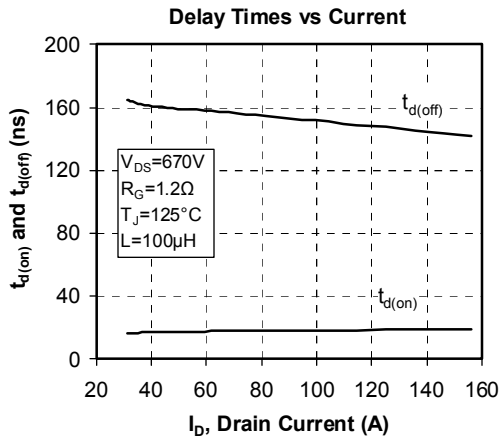
**Package outline**



**Typical Performance Curve**







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